1:00 PM - 1:30 PM

[19p-B5-1][JSAP Paper Award Speech](30 min.) Preparation of a Freestanding AlN Substrate from a Thick AlN Layer Grown by Hydride Vapor Phase Epitaxy on a Bulk AlN Substrate Prepared by Physical Vapor Transport

O: Yoshinao Kumagai1, Yuki Kubota2, Toru Nagashima1,2, Toru Kinoshita2, Rafael Dalmau3, Raoul Schlesser3, Baxter Moody3, Jinqiao Xie3, Hisashi Murakami1, Akinori Koukitu1, Zlatko Sitar3,4 (TUAT1, TOKUYAMA2, HexaTech3, NC State Univ.4)